

**PATENT APPLICATION****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of

Ichio YUDASAKA, Tatsuya SHIMODA, Sadao KANBE and Wakao MIYAZAWA

Application No.: 09/901,126

Filed: July 10, 2001

Docket No.: 040090.02

For: THIN FILM DEVICE PROVIDED WITH COATING FILM, LIQUID CRYSTAL  
PANEL AND ELECTRONIC DEVICE, AND METHOD FOR MAKING THE THIN  
FILM DEVICE

**PRELIMINARY AMENDMENT**

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 60-81 and 84-110 without prejudice to or disclaimer of the  
subject matter contained therein.

Please add new claims 111, 112 and 113 as follows:

--111. A process of forming thin film field effect transistors comprising the steps of:

forming a gate electrode on a substrate;

forming a gate insulator over said gate electrode;

forming a semiconducting layer on said insulator by ink-jet printing; and

forming source and drain contacts on said semiconducting layer.--

--112. The process of claim 111 wherein said formed semiconducting layer has a  
molecular structure containing plural monomer units.--